

Sheet 1 of 1

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DOCKET NUMBER (Optional) SALA:003

SERIAL NO.: 10/617,487

APPLICANT(s) SALAMA et al.

FILING DATE: July 11, 2003

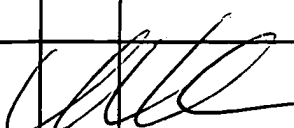
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
ML	US	4,754,310	6/88	Coe	357	13	
ML	US	5,216,275	6/93	Chen	257	493	
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ML	"High Voltage Thin Layer Devices (Resurf Devices)"; J.A. APPELS et al.; IEEE International Electron Device Meeting (IEDM); Dig. Tech Papers; pp. 238-241; 1979.
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EXAMINER  DATE CONSIDERED 7/24/04

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